



淄博圣诺

SR820 – SR8200

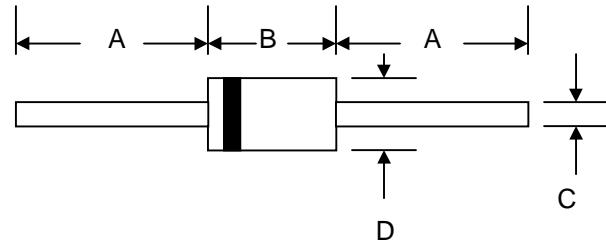


RoHS
2002/95/EC

8.0A SCHOTTKY BARRIER DIODE

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



Mechanical Data

- Case: DO-201AD, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 1.2 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- **Lead Free:** For RoHS / Lead Free Version

DO-201AD		
Dim	Min	Max
A	24.5	—
B	7.20	9.50
C	1.10	1.30
D	5.00	5.60

All Dimensions in mm

Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%.

Characteristic	Symbol	SR820	SR830	SR840	SR850	SR860	SR880	SR8100	SR8150	SR8200	Unit
Peak Repetitive Reverse Voltage	VRRM										
Working Peak Reverse Voltage	VRWM	20	30	40	50	60	80	100	150	200	V
DC Blocking Voltage	VR										
RMS Reverse Voltage	VR(RMS)	14	21	28	35	42	56	70	105	140	V
Average Rectified Output Current @ $T_L = 95^\circ\text{C}$ (Note 1)	Io										A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	Ifsm										A
Forward Voltage @ $I_F = 8.0\text{A}$	VFM										V
Peak Reverse Current @ $T_A = 25^\circ\text{C}$ At Rated DC Blocking Voltage @ $T_A = 100^\circ\text{C}$	IRM										mA
Typical Junction Capacitance (Note 2)	Cj										pF
Typical Thermal Resistance (Note 1)	R _{θJA}										°C/W
Operating and Storage Temperature Range	T _j , T _{STG}										°C
								-55 to +150			

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

